

μ PD5754T7A

R09DS0012EJ0100 Rev.1.00 Dec 22, 2010

SiGe/CMOS Integrated Circuit 4×2 IF Switch Matrix with Gain and Tone/Voltage Controller

FEATURES

4 independent IF channels, integral switching to channel input to either channel output

• 4×2 switch matrix with integrated IF amplifier and switch control - Tone/Voltage

- Switch's Enable mode is linked V_{CC} external pins

• Mirror reversal logic pattern of μ PD5739T7A

• Frequency range : f = 950 MHz to 2 150 MHz

 $\begin{array}{ll} \bullet & \text{High isolation} & : \text{ISL}_{D/U} = 30 \text{ dB TYP. @Worst mode} \\ \bullet & \text{Power gain} & : G_P = 18 \text{ dB TYP. } @ Z_S = Z_L = 50 \ \Omega \\ \end{array}$

• Power gain flatness : $\Delta G_P = 1.0 \text{ dB TYP}$.

• Surface mounting : 28-pin 5 × 5 mm square micro lead package (28-pin plastic QFN (0.5 mm pitch))

APPLICATIONS

• DBS IF switching

Multiswitch, Switch box

• 4 × 2 switching application for microwave signal

ORDERING INFORMATION

Part Number	Order Number	Package	Marking		Supplying Form
μPD5754T7A-E1	μPD5754T7A-E1-A	28-pin plastic QFN	D5754	•	Embossed tape 12 mm wide
		(0.5 mm pitch)		•	Pin 8 to 14 face the perforation side of the
		(Pb-Free)			tape
				•	Qty 2.5 kpcs/reel
				•	Dry packing specification (MSL 3 Equivalent)

Remark To order evaluation samples, please contact your nearby sales office.

Part number for sample order: μ PD5754T7A

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Supply Voltage	V_{DD} ,	+4.0	V
	$V_{CC}1, V_{CC}2$		
Power Dissipation Note	P_D	1.465	W
Storage Temperature	T_{stg}	-55 to +125	°C
Operating Ambient Temperature	T_A	-40 to +85	°C
Input Power	P _{in}	+5	dBm
POLA Control Input Voltage	V_{POLA}	+25	V
(POLA1 and POLA2)			
TONE Signal Input Voltage	V_{TONE}	1	V_{p-p}

Note: Mounted on double-sided copper-clad $50 \times 50 \times 0.51$ mm laminates PWB, $T_A = +85^{\circ}C$

RECOMMENDED OPERATING RANGE (T_A = +25°C, unless otherwise specified)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage Note	V_{DD} ,	+3.0	+3.3	+3.6	V
	$V_{CC}1, V_{CC}2$				
Operating Ambient Temperature	T _A	-40	+25	+85	°C
POLA Control Input Voltage	V_{POLA}	0	_	21	V
TONE Signal Frequency	f _{TONE}	18	22	26	kHz
TONE Signal Input Voltage	V_{TONE}	0.4	0.6	0.8	V_{p-p}

Note: $V_{CC}1 = V_{CC}2 = V_{DD}$

ELECTRICAL CHARACTERISTICS $(T_A = +25^{\circ}C, V_{DD} = V_{CC}1 = V_{CC}2 = +3.3 \text{ V}, Z_S = Z_L = 50 \Omega \text{ for each port, worst mode, unless otherwise specified)}$

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Total Supply Current	I _{CC}	non–RF, 2 channels active	33	40	50	mA
		total current of I _{CC} 1, I _{CC} 2, and I _{DD}				
Power Gain 1	G _P 1	$P_{in} = -30 \text{ dBm}, f = 0.95 \text{ GHz}$	15	18	21	dB
Power Gain 2	G _P 2	$P_{in} = -30 \text{ dBm}, f = 2.15 \text{ GHz}$	14.5	17.5	20.5	dB
Isolation D/U-ratio 2 Note	ISL _{D/U} 2	$P_{in} = -30 \text{ dBm}, f = 2.15 \text{ GHz}$	25	30	-	dB
Gain 1 dB Compression	P _{O (1 dB)} 1	f = 0.95 GHz	5	8	_	dBm
Output Power 1						
Gain 1 dB Compression	P _{O (1 dB)} 2	f = 2.15 GHz	3	6	_	dBm
Output Power 2						
Output Return Loss 1	RL _{out} 1	$P_{in} = -30 \text{ dBm}, f = 0.95 \text{ GHz}$	10	14	_	dB
Output Return Loss 2	RL _{out} 2	P _{in} = -30 dBm, f = 2.15 GHz	10	12.5	_	dB
Noise Figure 1	NF1	f = 0.95 GHz	_	10.5	12.5	dB
Noise Figure 2	NF2	f = 2.15 GHz	_	11.5	13.5	dB
POLA Control Threshold Voltage,	V_{th_POLA}	OFF to ON	14	14.5	15.5	V
Channel Selection						
TONE Signal Threshold	V_{th_TONE}	f _{TONE} = 22 kHz, Duty Cycle = 50%,	0.1	0.15	0.35	V_{p-p}
Voltage, Channel Selection		pulse wave, OFF to ON				

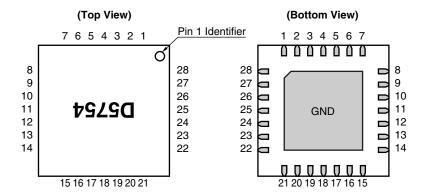
Note: Isolation D/U (\underline{D} esire/ \underline{U} n-desire) ratio = |(Signal Leakage (off-state)) – (Power Gain (on-state))| at worst mode

STANDARD CHARACTERISTICS FOR REFERENCE (T_A = +25°C, V_{DD} = V_{CC}1 = V_{CC}2 = +3.3 V, Z_S = Z_L = 50 Ω for each port, worst mode, unless otherwise specified)

Parameter	Symbol	Test Conditions	Reference Value	Unit
Supply Current of V _{CC} 1, V _{CC} 2	I _{CC} 1, I _{CC} 2		19	mA
Supply Current of V _{DD}	I _{DD}		2.0	mA
Gain Flatness	⊿G _P 1	$P_{in} = -30 \text{ dBm},$	1.0	dB
Differential Gain Between Active	⊿G _P 2	f = 0.95 GHz to 2.15 GHz	1.0	dB
Channels				
Gain Change, selected channel	⊿G _P 3		1.0	dB
Isolation D/U Ratio 1 Note	ISL _{D/U} 1	P _{in} = -30 dBm, f = 0.95 GHz	30	dB
Input Return Loss 1	RL _{in} 1	P _{in} = -30 dBm, f = 0.95 GHz	13	dB
Input Return Loss 2	RL _{in} 2	P _{in} = -30 dBm, f = 2.15 GHz	10	dB
Output 3rd Order Intercept Point	OIP ₃ 1	f1 = 950 MHz,	19	dBm
1		f2 = 951 MHz		
Output 3rd Order Intercept Point	OIP ₃ 2	f1 = 2 150 MHz,	15	dBm
2		f2 = 2 151 MHz		
2nd Order Intermodulation	IM_2	f1 = 950 MHz,	44	dBc
Distortion		f2 = 951 MHz,		
		P _{out} = –5 dBm/tone		
2nd Harmonics	2f0	$f0 = 1.0 \text{ GHz}, P_{out} = -15 \text{ dBm}$	60	dBc
K factor 1	K1	$P_{in} = -30 \text{ dBm}, f = 0.95 \text{ GHz}$	2.5	_
K factor 2	K2	P _{in} = -30 dBm, f = 2.15 GHz	2.5	_
POLA Control Current	I _{POLA}	V _{POLA} = 21 V	50	μΑ
POLA Switching Time	T _{POLA}	V _{POLA} = 18 V, OFF to ON	1.0	μs
TONE Switching Time	T _{TONE}	f _{TONE} = 22 kHz, Duty Cycle = 50%,	250	μs
		pulse wave, V_{TONE} = 600 m V_{p-p} , OFF to ON		

Note: Isolation D/U (\underline{D} esire/ \underline{U} n-desire) ratio = |(Signal Leakage (off-state)) – (Power Gain (on-state))| at worst mode

PIN CONNECTIONS



Pin No.	Pin Name	Pin No.	Pin Name	Pin No.	Pin Name	Pin No.	Pin Name
1	V _{CC} 1	8	GND	15	IN-D	22	GND
2	OUT1	9	IN-B	16	GND	23	POLA2
3	GND	10	GND	17	GND	24	TONE2
4	GND	11	GND	18	GND	25	V_{DD}
5	GND	12	GND	19	GND	26	TONE1
6	GND	13	IN-C	20	OUT2	27	POLA1
7	IN-A	14	GND	21	V _{CC} 2	28	GND

Remark Heat Sink (Bottom side): GND

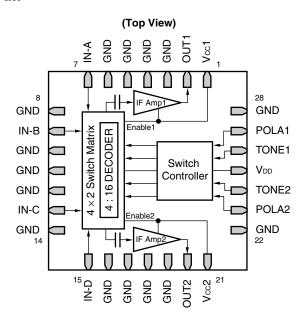
TRUTH TABLE OF SWITCHING BY CONDITION OF CONTROL VOLTAGE

	State		-	out to State						
No.	Mode)	OUT1	OUT2	TONE1	POLA1	TONE2	POLA2	V _{cc} 1 (Enable1)	V _{cc} 2 (Enable2)
1		DD		IN-D	22 kHz	Low	22 kHz	Low	3.3 V	3.3 V
2		DC	IN-D	IN-C	22 kHz	Low	0	Low	3.3 V	3.3 V
3		DB	ט-וווי	IN-B	22 kHz	Low	0	High	3.3 V	3.3 V
4		DA		IN-A	22 kHz	Low	22 kHz	High	3.3 V	3.3 V
5		CD		IN-D	0	Low	22 kHz	Low	3.3 V	3.3 V
6		CC	IN-C	IN-C	0	Low	0	Low	3.3 V	3.3 V
7	5	СВ	IIV-C	IN-B	0	Low	0	High	3.3 V	3.3 V
8	Both OUTs	CA		IN-A	0	Low	22 kHz	High	3.3 V	3.3 V
9	Enabled	BD		IN-D	0	High	22 kHz	Low	3.3 V	3.3 V
10	Lilabica	ВС	INID	IN-C	0	High	0	Low	3.3 V	3.3 V
11		BB	IN-B	IN-B	0	High	0	High	3.3 V	3.3 V
12		BA		IN-A	0	High	22 kHz	High	3.3 V	3.3 V
13		AD		IN-D	22 kHz	High	22 kHz	Low	3.3 V	3.3 V
14		AC	IN-A	IN-C	22 kHz	High	0	Low	3.3 V	3.3 V
15		AB	IIN-A	IN-B	22 kHz	High	0	High	3.3 V	3.3 V
16		AA		IN-A	22 kHz	High	22 kHz	High	3.3 V	3.3 V
17		ND		IN-D	Any Note	Any Note	22 kHz	Low	0	3.3 V
18	OUT1	NC	None	IN-C	Any Note	Any Note	0	Low	0	3.3 V
19	Disabled	NB	NOHE	IN-B	Any Note	Any Note	0	High	0	3.3 V
20		NA		IN-A	Any Note	Any Note	22 kHz	High	0	3.3 V
21		DN	IN-D		22 kHz	Low	Any Note	Any Note	3.3 V	0
22	OUT2	CN	IN-C	None	0	Low	Any Note	Any ^{Note}	3.3 V	0
23	Disabled	BN	IN-B	NOILE	0	High	Any Note	Any Note	3.3 V	0
24		AN	IN-A		22 kHz	High	Any ^{Note}	Any Note	3.3 V	0
25	Both OUTs D	isabled	None	None	Any ^{Note}	Any Note	Any Note	Any Note	0	0

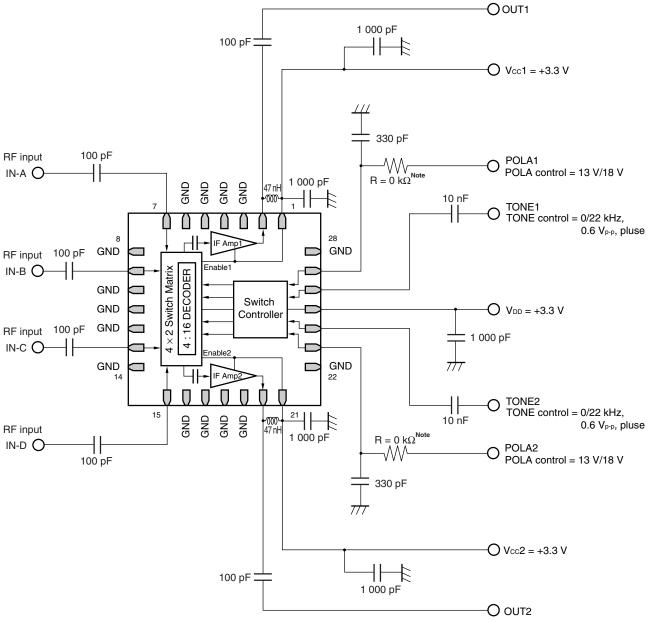
Note: Any means High or Low, 22 kHz or 0.

Remark Low: under +14 Vdc, High: +15.5 to +19.0 Vdc, V_{DD} = +3.3 Vdc

FUNCTIONAL DIAGRAM



EVALUATION CIRCUIT



Note: R = 0 k Ω (at POLA control = 13 V/18 V) = 5.6 k Ω (at POLA control = 14 V/18 V)

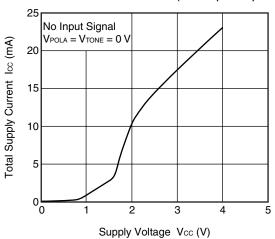
Remark Low: under +14 Vdc, High: +15.5 to +19.0 Vdc, V_{DD} = +3.3 Vdc

The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

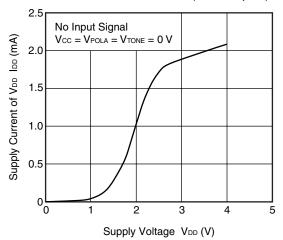
TYPICAL CHARACTERISTICS

(T_A = +25°C, V_{DD} = V_{CC}1 = V_{CC}2 = +3.3 V, Z_S = Z_L = 50 Ω for each port, worst mode, unless otherwise specified)

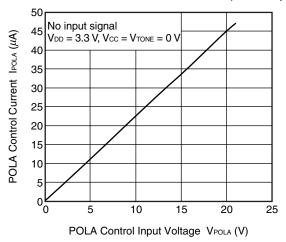
TOTAL SUPPLY CURRENT vs. SUPPLY VOLTAGE (IF-Amplifier part)



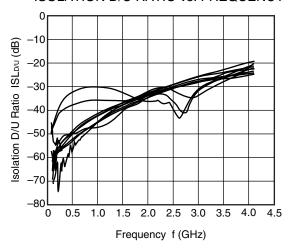
SUPPLY CURRENT OF VDD vs. SUPPLY VOLTAGE (Control part)



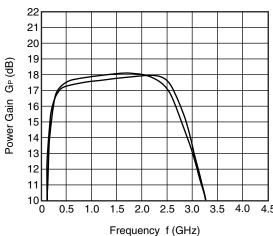
POLA CONTROL CURRENT vs.
POLA CONTROL INPUT VOLTAGE (Control part)



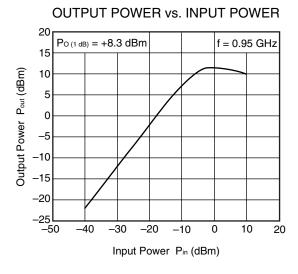
ISOLATION D/U RATIO vs. FREQUENCY

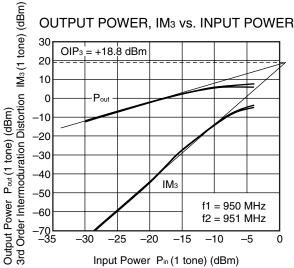


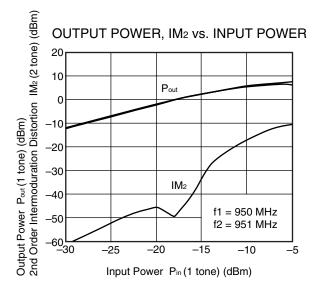
POWER GAIN vs. FREQUENCY



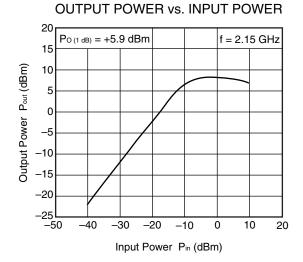
Remark The graphs indicate nominal characteristics.

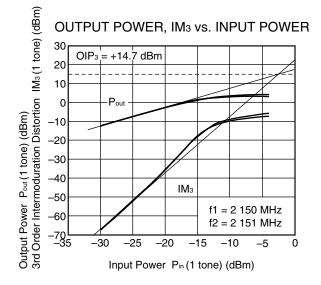


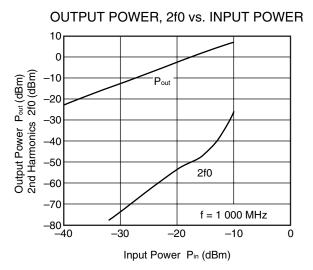


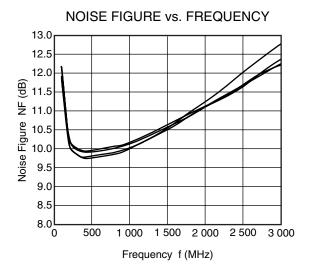


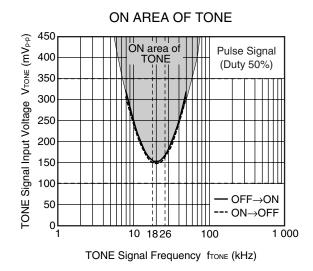
Remark The graphs indicate nominal characteristics.

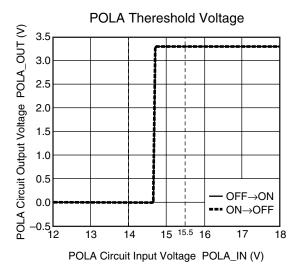








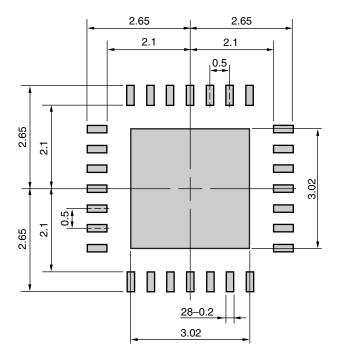




Remark The graphs indicate nominal characteristics.

MOUNTING PAD LAYOUT DIMENSIONS

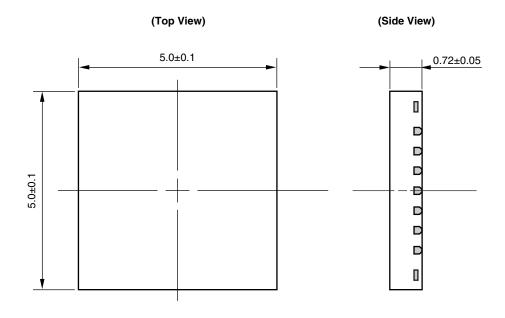
28-PIN 5×5 mm SQUARE MICRO LEAD PACKAGE (28-PIN PLASTIC QFN (0.5 mm pitch)) (UNIT: mm)

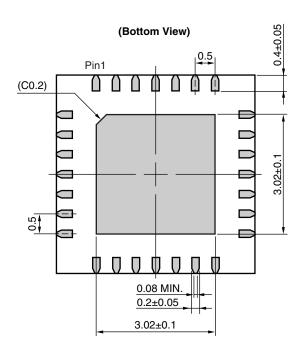


Remark The mounting pad layout in this document is for reference only.

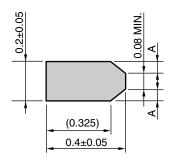
PACKAGE DIMENSIONS

28-PIN 5×5 mm SQUARE MICRO LEAD PACKAGE (28-PIN PLASTIC QFN (0.5 mm pitch)) (UNIT: mm)





(Dimensions of Each Pin Part)



Remark A>0

(): Reference value

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature)	: 260°C or below	IR260
	Time at peak temperature	: 10 seconds or less	
	Time at temperature of 220°C or higher	: 60 seconds or less	
	Preheating time at 120 to 180°C	: 120±30 seconds	
	Maximum number of reflow processes	: 3 times	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	
Partial Heating	Peak temperature (terminal temperature)	: 350°C or below	HS350
	Soldering time (per side of device)	: 3 seconds or less	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	

CAUTION

Do not use different soldering methods together (except for partial heating).

Revision History

μ PD5754T7A Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Dec 22, 2010	_	First edition issued	

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